





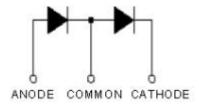
406DMQ200 SCHOTTKY RECTIFIER



Features

- 175°C T_J operation
- · Center tap module
- High purity, high temperature epoxy encapsulation for
- enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- · High current switching power supply
- Plating power supply
- Free-Wheeling diodes
- Reverse battery protection
- Converters
- UPS System
- Welding

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	-	200	V
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @Tc =121°C, rectangular wave form	200(Per Leg) 400(Per Device)	А
Peak One Cycle Non-Repetitive Surge Current (Per Leg)	I _{FSM}	8.3 ms, half Sine pulse	3840	Α

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V _{F1}	@ 200A, Pulse, T _J = 25 °C @ 400A, Pulse, T _J = 25 °C	0.85 -	0.99 1.15	V
	V _{F2}	@ 200A, Pulse, T _J = 125 °C @ 400A, Pulse, T _J = 125 °C	0.70 -	0.79 0.92	V
Reverse Current(Per Leg)*	I _{R1}	$@V_R = \text{rated } V_{R,} T_J = 25 ^{\circ}\text{C}$	0.001	10	mA
	I _{R2}	$@V_R = \text{rated } V_{R_i} T_J = 125 ^{\circ}\text{C}$	1	90	mA
Junction Capacitance(Per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	3000	5200	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs
Insulation Voltage	V _{RMS}	-	-	1000	V

^{*} Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification		Units
Junction Temperature	TJ	-	-55 to +175		°C
Storage Temperature	T _{stg}	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case(Per leg)	R _θ JC	DC operation	0.4	0	°C/W
Typical Thermal Resistance Junction to Case(Per package)	R _θ JC	DC operation	0.2	0	°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{\theta cs}$	Mounting surface, smooth and greased	0.10		°C/W
Mounting Torque	T _M	-	Mounting Torque	24(min) 35(max)	- Kg-cm
			Terminal Torque	35(min) 46(max)	
Approximate Weight	wt	-	79 g		g
Case Style	PRM4 Isolated				

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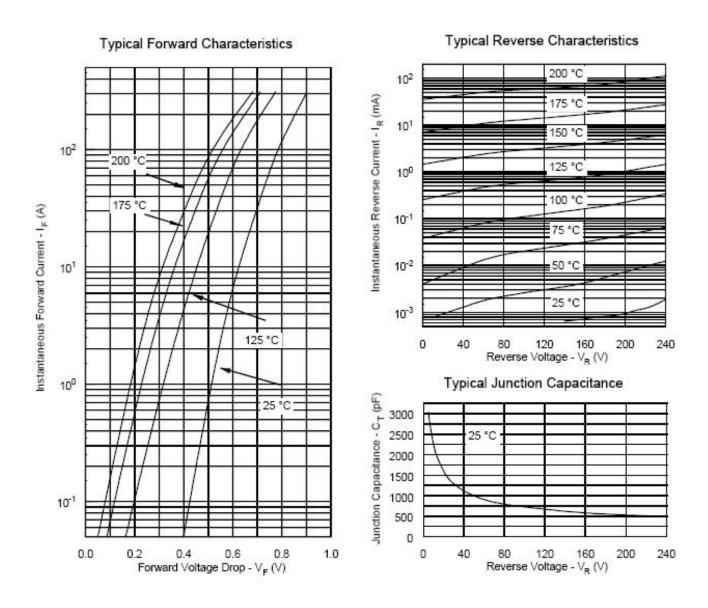
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Ratings and Characteristics Curves



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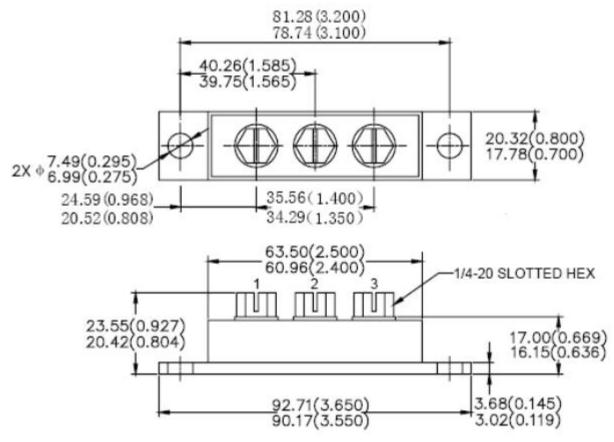
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Mechanical Dimensions PRM4 Isolated(Millimeters/Inches)



Please Note: Suffix "R" Denotes For Reversed Polarity

Marking Diagram



Where XXXX is YYWW

406DMQ200 = Part name SS = SS YY = Year WW = Week

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping	
406DMQ200	PRM4 Isolated (Pb-Free)	9 pcs/box	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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